

R-C Thermal Model Parameters

DESCRIPTION

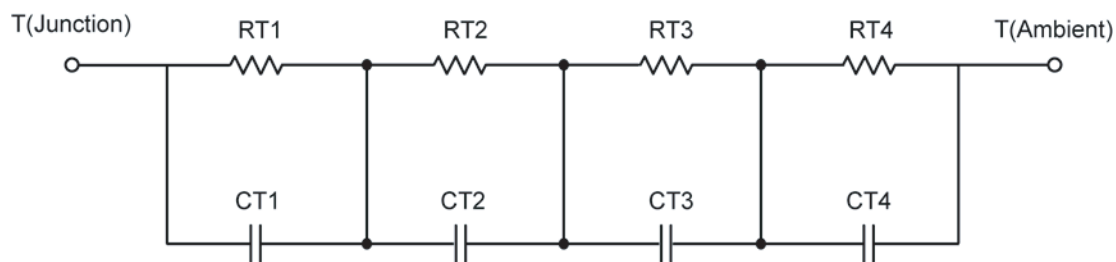
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	6.6978	N/A	12.8328
RT2	32.0141	N/A	3.7210
RT3	23.6912	N/A	6.5904
RT4	47.5969	N/A	13.8558
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	409.8501 u	N/A	4.2079 m
CT2	58.1899 m	N/A	387.0973 u
CT3	9.1217 m	N/A	298.2415 m
CT4	1.4430	N/A	38.6071 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	9.8743	N/A	4.3216
RF2	31.1731	N/A	16.3836
RF3	24.7323	N/A	13.6479
RF4	44.2203	N/A	2.6469
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	703.3799 u	N/A	302.8478 u
CF2	9.5548 m	N/A	3.6648 m
CF3	71.2050 m	N/A	45.9113 m
CF4	1.5320	N/A	269.4461 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

